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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.466US1	Serial No. 09/069,668
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: April 29, 1998	Group: 2814

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes / No
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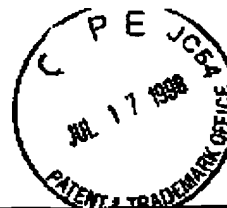
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